

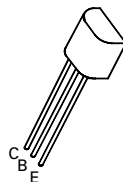
PNP SILICON PLANAR MEDIUM POWER HIGH VOLTAGE TRANSISTORS

ISSUE 2 – JULY 94

ZTX756 ZTX757

FEATURES

- * 300 Volt V_{CEO}
- * 0.5 Amp continuous current
- * $P_{tot} = 1$ Watt



E-Line
TO92 Compatible

ABSOLUTE MAXIMUM RATINGS.

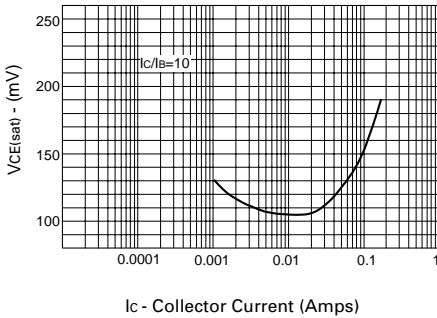
| PARAMETER | SYMBOL | ZTX756 | ZTX757 | UNIT |
|--|----------------|--------|-------------|-------------|
| Collector-Base Voltage | V_{CBO} | -200 | -300 | V |
| Collector-Emitter Voltage | V_{CEO} | -200 | -300 | V |
| Emitter-Base Voltage | V_{EBO} | | -5 | V |
| Peak Pulse Current | I_{CM} | | -1 | A |
| Continuous Collector Current | I_C | | -0.5 | A |
| Power Dissipation at $T_{amb}=25^{\circ}C$ | P_{tot} | | 1 | W |
| Operating and Storage Temperature Range | $T_j; T_{stg}$ | | -55 to +200 | $^{\circ}C$ |

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

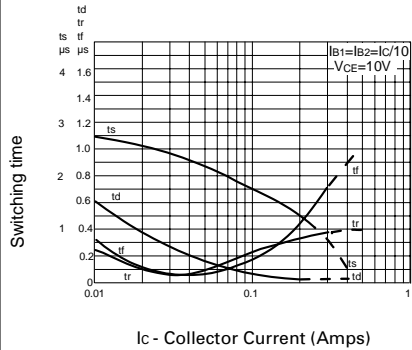
| PARAMETER | SYMBOL | ZTX756 | | ZTX757 | | UNIT | CONDITIONS. |
|---------------------------------------|---------------|----------|------|----------|------|------|---|
| | | MIN. | MAX. | MIN. | MAX. | | |
| Collector-Base Breakdown Voltage | $V_{(BR)CBO}$ | -200 | | -300 | | V | $I_C = -100\mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | -200 | | -300 | | V | $I_C = -10mA, I_B = 0^*$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -5 | | -5 | | V | $I_E = -100\mu A, I_C = 0$ |
| Collector Cut-Off Current | I_{CBO} | | -100 | | -100 | nA | $V_{CB} = -160V, I_E = 0$ $V_{CB} = -200V, I_E = 0$ |
| Emitter Cut-Off Current | I_{EBO} | | -100 | | -100 | nA | $V_{EB} = -3V, I_C = 0$ |
| Collector-Emitter Saturation Voltage | $V_{CE(sat)}$ | | -0.5 | | -0.5 | V | $I_C = -100mA, I_B = -10mA^*$ |
| Base-Emitter Saturation Voltage | $V_{BE(sat)}$ | | -1.0 | | -1.0 | V | $I_C = -100mA, I_B = -10mA^*$ |
| Base-Emitter Turn-On Voltage | $V_{BE(on)}$ | | -1.0 | | -1.0 | V | $I_C = -100mA, V_{CE} = -5V^*$ |
| Static Forward Current Transfer Ratio | h_{FE} | 50 40 | | 50 40 | | | $I_C = -100mA, V_{CE} = -5V^*$ $I_C = -10mA, V_{CE} = -5V^*$ |
| Transition Frequency | f_T | 30 | | 30 | | MHz | $I_C = -10mA, V_{CE} = -20V$ $f = 20MHz$ |
| Output Capacitance | C_{obo} | | 20 | | 20 | pF | $V_{CB} = -20V, f = 1MHz$ |

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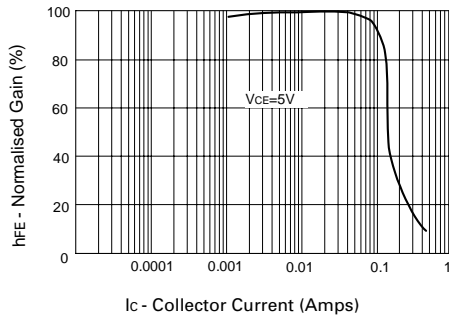
TYPICAL CHARACTERISTICS



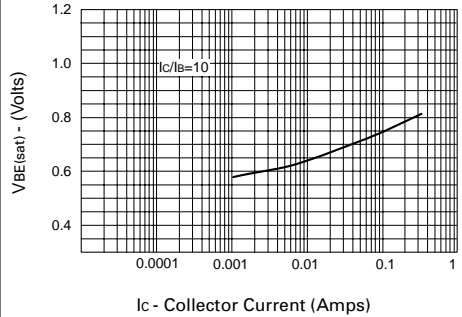
$V_{CE(sat)}$ v I_C



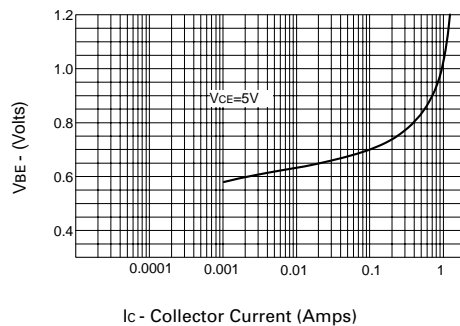
Switching Speeds



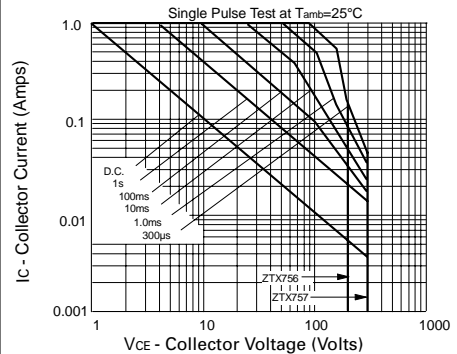
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area

单击下面可查看定价，库存，交付和生命周期等信息

[>>Diodes Incorporated\(达尔科技\)](#)